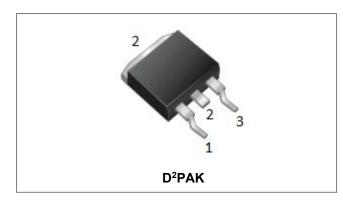


# SDURB860A

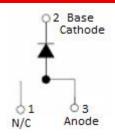
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# SDURB860A ULTRAFAST RECTIFIER



# **Circuit Diagram**



### **Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

#### Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- "-A" is an AEC-Q101 qualified device
- Terminals finish: 100% Pure Tin
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Maximum Ratings:**

| Characteristics  | Symbol   | Condition  | Max. | Units |
|--|--|--|------|-------|
| Peak Repetitive Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage | V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | -  | 600  | V     |
| Average Rectified Forward Current  | I <sub>F (AV)</sub>                                    | 50% duty cycle @Tc=100°C,<br>rectangular wave form | 8    | A     |
| Peak One Cycle Non-Repetitive Surge<br>Current   | I <sub>FSM</sub>                                       | 8.3ms, Half Sine pulse                             | 80   | А     |

## Electrical Characteristics:

| Characteristics       | Symbol          | Condition  | Тур. | Max. | Units |
|-----------------------|-----------------|--|------|------|-------|
| Forward Voltage Drop* | V <sub>F1</sub> | @ 8A, Pulse, T <sub>J</sub> = 25°C                     | 1.6  | 2.0  | V     |
| Reverse Current*      | I <sub>R1</sub> | $@V_R = rated V_R, T_J = 25^{\circ}C$                  | 0.3  | 8    | μA    |
|                       | I <sub>R2</sub> | @ $V_R$ = rated V,T <sub>J</sub> = 125°C               | 0.2  | 1    | mA    |
| Reverse Recovery Time | t <sub>rr</sub> | $I_F$ =500mA, $I_R$ =1A,and $I_m$ =250mA, $T_J$ = 25°C | 32   | 35   | ns    |

\* Pulse width < 300 µs, duty cycle < 2%

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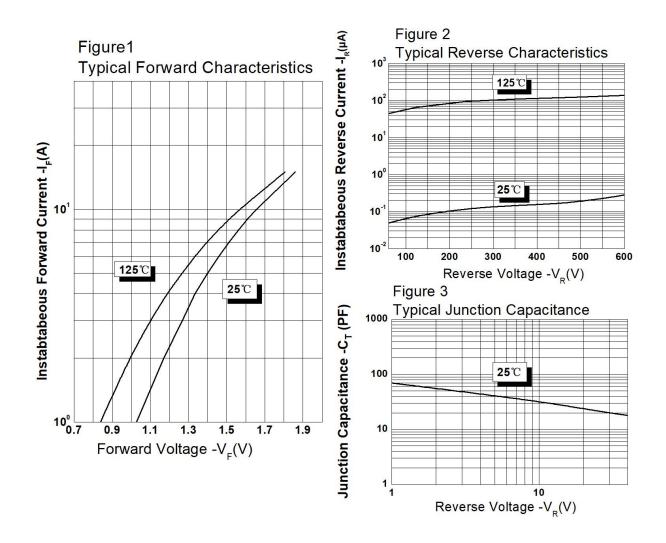


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### **Thermal-Mechanical Specifications:**

| Characteristics                                | Symbol             | Condition    | Specification | Units |
|--|--------------------|--------------|---------------|-------|
| Junction Temperature                           | TJ                 | -            | -55 to +150   | °C    |
| Storage Temperature                            | T <sub>stg</sub>   | -            | -55 to +150   | °C    |
| Typical Thermal Resistance Junction to Ambient | R <sub>0JA</sub>   | DC operation | 25            | °C/W  |
| Approximate Weight                             | wt                 | -            | 1.85          | g     |
| Case Style                                     | D <sup>2</sup> PAK |              |               |       |

### **Ratings and Characteristics Curves**



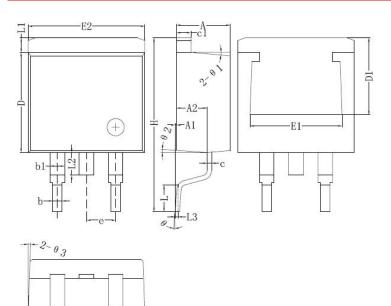


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## Mechanical Dimensions D<sup>2</sup>PAK



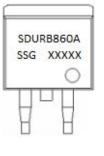
| Symbol     | Dimensions in millimeters |       |  |
|------------|---------------------------|-------|--|
| - <b>,</b> | Min.                      | Max.  |  |
| A          | 4.06                      | 4.83  |  |
| A1         | 0                         | 0.26  |  |
| b          | 0.51                      | 0.99  |  |
| b1         | 1.14                      | 1.78  |  |
| с          | 0.31                      | 0.74  |  |
| c1         | 1.14                      | 1.65  |  |
| D          | 8.38                      | 8.65  |  |
| D1         | 6.86                      |       |  |
| E1         | 6.22                      |       |  |
| E2         | 9.65                      | 10.67 |  |
| е          | 2.54BSC                   |       |  |
| Н          | 14.60                     | 15.88 |  |
| L          | 1.78                      | 2.80  |  |
| L1         | -                         | 1.68  |  |
| L2         | -                         | 1.78  |  |
| L3         | 0.255BSC                  |       |  |
| Θ          | 0                         | 8°    |  |

## **Ordering Information**

| Device      | Package            | Shipping      |
|-------------|--------------------|---------------|
| SDURB860A   | D <sup>2</sup> PAK | 800pcs / reel |
| SDURB860ATR | D <sup>2</sup> PAK | 800pcs / reel |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



Where XXXXX is YYWWL

- = Device Type
- = Package type
- = Forward Current (8A)
- = Reverse Voltage(600V) = A
- = A = SSG

SDUR

В

8

60

A SSG

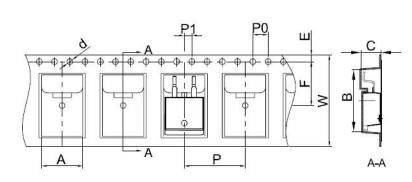
YΥ

WW L

- = 336 = Year
- = Week
- = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

## Carrier Tape Specification D<sup>2</sup>PAK



| SYMBOL | Millimeters |       |  |
|--------|-------------|-------|--|
| STWDUL | Min.        | Max.  |  |
| A      | 10.70       | 10.90 |  |
| В      | 16.03       | 16.23 |  |
| С      | 5.11        | 5.31  |  |
| d      | 1.45        | 1.65  |  |
| E      | 1.65        | 1.85  |  |
| F      | 11.40       | 11.60 |  |
| P0     | 3.90        | 4.10  |  |
| Р      | 15.90       | 16.10 |  |
| P1     | 1.90        | 2.10  |  |
| W      | 23.90       | 24.30 |  |

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